Andreas Lesnik

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/5559312/publications.pdf

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11	272	1163117 8	1281871 11
papers	citations	h-index	g-index

11	11	11	441
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Two charge states of the <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi mathvariant="normal">C</mml:mi><mml:mi mathvariant="normal">N</mml:mi></mml:msub></mml:math> acceptor in GaN: Evidence from photoluminescence. Physical Review B, 2018, 98, .	3.2	84
2	Properties of Câ€doped GaN. Physica Status Solidi (B): Basic Research, 2017, 254, 1600708.	1.5	33
3	Methodology for the investigation of threading dislocations as a source of vertical leakage in AlGaN/GaN-HEMT heterostructures for power devices. Journal of Applied Physics, 2019, 125, .	2.5	30
4	Twin domain imaging in topological insulator Bi₂Te₃ and Bi₂Se₃ epitaxial thin films by scanning X-ray nanobeam microscopy and electron backscatter diffraction. Journal of Applied Crystallography, 2017, 50, 369-377.	4.5	28
5	On reduction of current leakage in GaN by carbon-doping. Applied Physics Letters, 2016, 109, .	3.3	25
6	Leakage currents and Fermi-level shifts in GaN layers upon iron and carbon-doping. Journal of Applied Physics, 2017, 122, .	2.5	23
7	Growth of AlInN/GaN distributed Bragg reflectors with improved interface quality. Journal of Crystal Growth, 2015, 414, 105-109.	1.5	22
8	Metalorganic chemical vapor phase epitaxy of narrow-band distributed Bragg reflectors realized by GaN:Ge modulation doping. Journal of Crystal Growth, 2016, 440, 6-12.	1.5	11
9	Characterization of AlInN/AlN/GaN FET structures using x-ray diffraction, x-ray reflectometry and grazing incidence x-ray fluorescence analysis. Journal Physics D: Applied Physics, 2014, 47, 355106.	2.8	6
10	Observation of individual stacking faults in GaN microcrystals by x-ray nanodiffraction. Applied Physics Letters, 2017, 110, .	3.3	6
11	Enhanced sheet carrier densities in polarization controlled AlInN/AlN/GaN/InGaN field-effect transistor on Si (111). AIP Advances, 2015, 5, .	1.3	4